

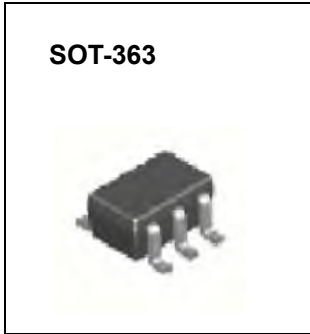
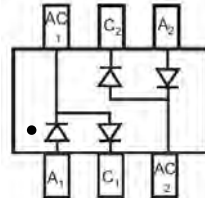


### SOT-363 Plastic-Encapsulate Diode

#### SWITCHING DIODE

#### FEATURES

- Fast Switching Speed
- Ultra-Small Surface Mount Package
- For General Purpose Switching Applications
- High Conductance
- **Pb-Free package is available**  
RoHS product for packing code suffix "G"  
Halogen free product for packing code suffix "H"
- Moisture Sensitivity Level 1



#### MAKING: KJG

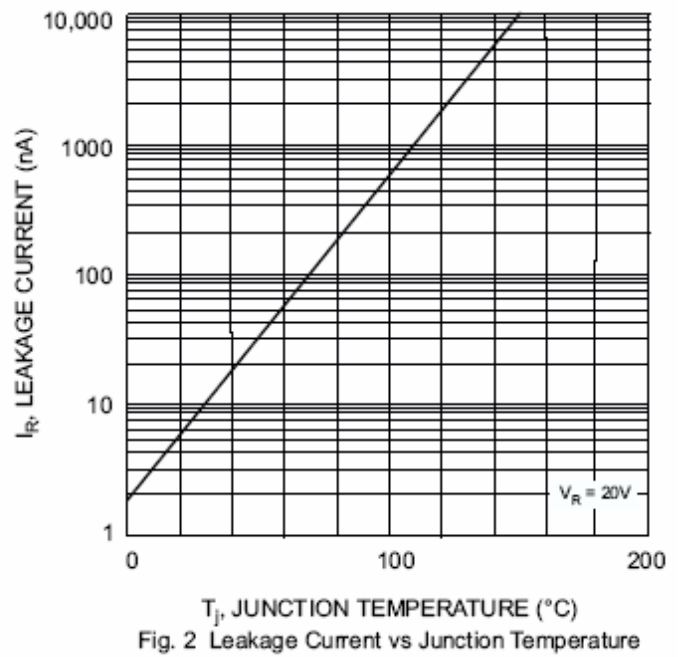
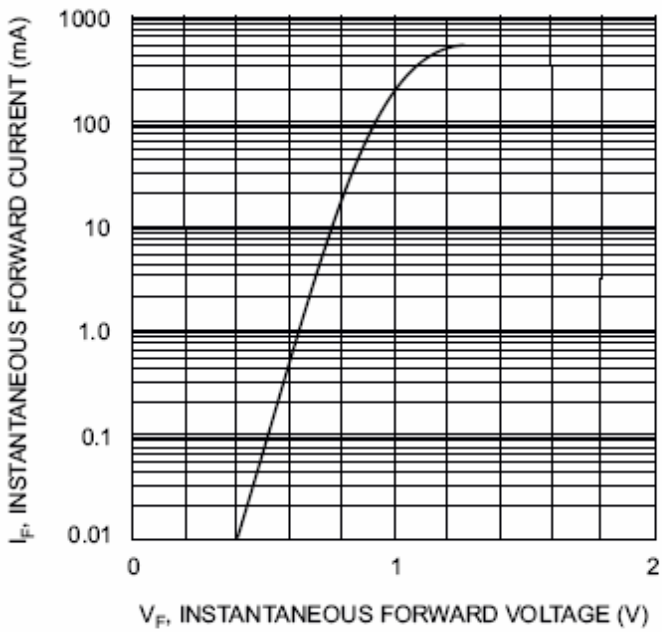
#### Maximum Ratings @T<sub>A</sub>=25°C

Parameter	Symbol	Limits	Unit
Peak Repetitive Peak reverse voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	75	V
Forward Continuous Current	I <sub>FM</sub>	300	mA
Average Rectified Output Current	I <sub>O</sub>	150	mA
Non-Repetitive Peak Forward Surge Current	I <sub>FSM</sub>	2 1	A
		@ t = 1.0µs @ t = 1.0s	
Power Dissipation	P <sub>D</sub>	200	mW
Thermal Resistance Junction to Ambient Air	R <sub>θJA</sub>	625	°C/W
Operating Junction Temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>STG</sub>	-55-150	°C

#### ELECTRICAL CHARACTERISTICS (T<sub>amb</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	V <sub>(BR)R</sub>	I <sub>R</sub> = 2.5µA	75		V
Reverse voltage leakage current	I <sub>R</sub>	V <sub>R</sub> =75V V <sub>R</sub> =20V		2.5 0.025	µA
Forward voltage	V <sub>F</sub>	I <sub>F</sub> =1mA I <sub>F</sub> =10mA I <sub>F</sub> =50mA I <sub>F</sub> =150mA		715 855 1000 1250	mV
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> =0, f=1MHz		2	pF
Reveres recovery time	t <sub>rr</sub>	I <sub>F</sub> =I <sub>R</sub> =10mA, I <sub>rr</sub> =0.1×I <sub>R</sub> , R <sub>L</sub> =100Ω		4	nS

**Typical Characteristics**

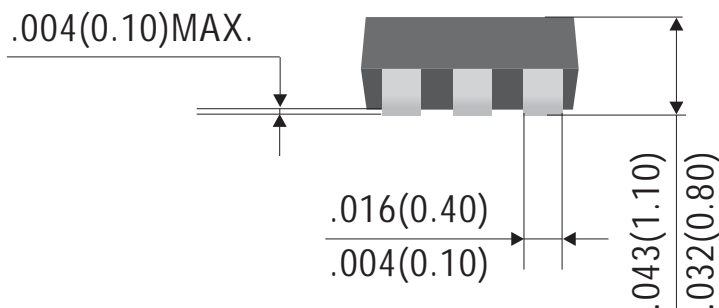
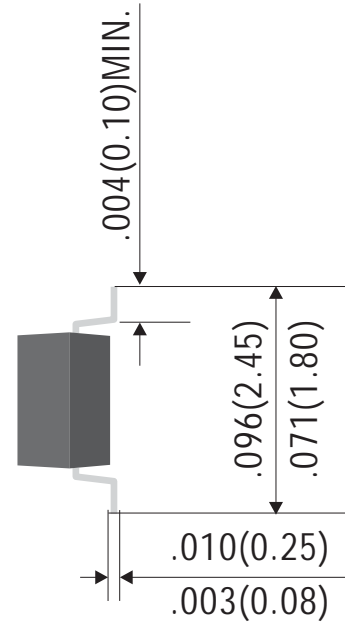
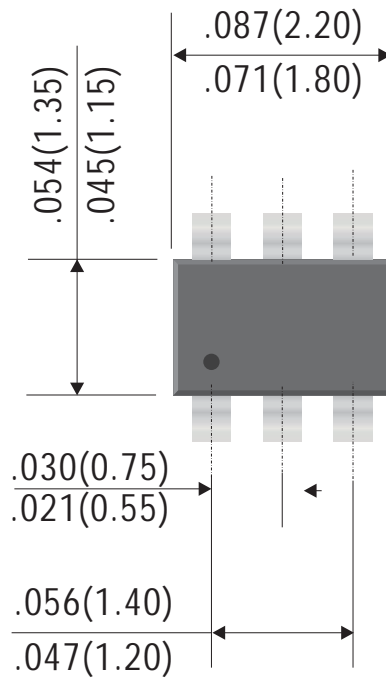




## SOT-363 Plastic-Encapsulate Diode

### Outline Drawing

### SOT-363



Dimensions in inches and (millimeters)